

N-channel 100 V 4.3 mΩ standard level MOSFET in I2PAK Rev. 1 — 31 October 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

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- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>		-	6.6	7.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 13</u>	[2]	-	3.7	4.3	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 75 A; V_{DS} = 50 V;		-	49	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	170	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; Unclamped		-	-	537	mJ

[1] Continuous current limited by package

[2] Measured 3 mm from package.

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N-channel 100 V 4.3 mΩ standard level MOSFET in I2PAK

2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT226 (I2PAK)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

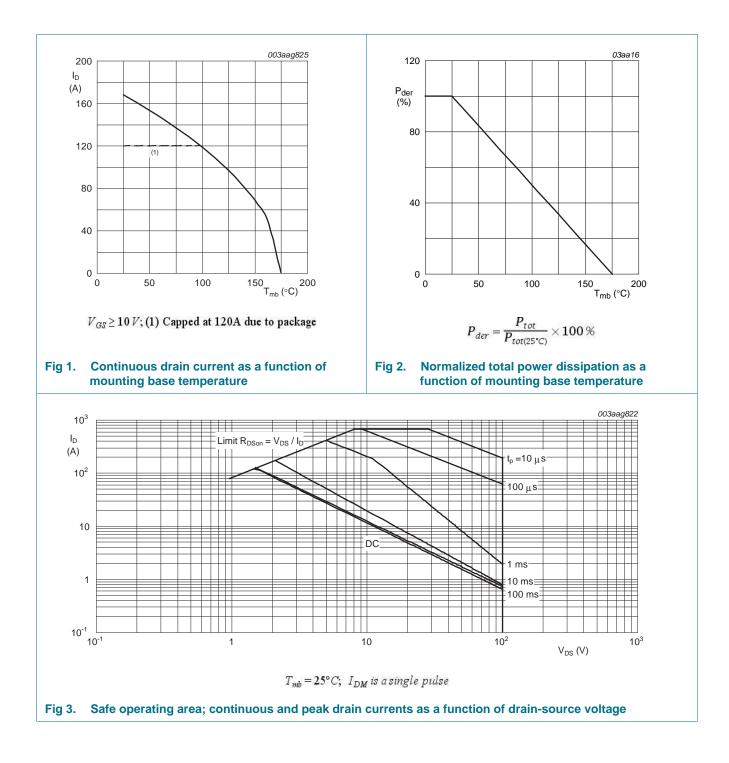
Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
gate-source voltage			-20	20	V
drain current	V_{GS} = 10 V; T_j = 100 °C; see <u>Figure 1</u>		-	119	А
	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	120	А
peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	673	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
storage temperature			-55	175	°C
junction temperature			-55	175	°C
peak soldering temperature			-	260	°C
diode					
source current	T _{mb} = 25 °C	[1]	-	120	А
peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	673	А
Jgedness					
non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω ; Unclamped		-	537	mJ
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature peak soldering temperature diode source current peak source current peak source current peak source current peak source current	$\begin{array}{ll} drain-source \ voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ \\ drain-gate \ voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega \\ \\ gate-source \ voltage & & & & & & \\ \\ drain \ current & V_{GS} = 10 \ \text{V}; \ T_{j} = 100 \ ^{\circ}\text{C}; \ see \ Figure \ 1} \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure \ 1} \\ \\ peak \ drain \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C}; \\ see \ Figure \ 3} \\ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure \ 2} \\ storage \ temperature & & & \\ junction \ temperature & & \\ peak \ soldering \ temperature & & \\ peak \ soldering \ temperature & & & \\ \hline diode & & & \\ source \ current & T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \mu s; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ peak \ source \ current & pulsed; \ t_{p} \leq 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_{D} = 120 \ \text{A}; \\ \end{array}$	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} \\ \mbox{drain current} & \frac{V_{GS} = 10 \ V; \ T_j = 100 \ {}^\circ\mbox{C}; \ see \ Figure 1}{V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 1} & [1] \\ \mbox{peak drain current} & pulsed; \ t_p \le 10 \ \mu s; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2} \\ \mbox{total power dissipation} & T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2} \\ \mbox{storage temperature} \\ \mbox{junction temperature} \\ \mbox{peak soldering temperature} \\ \mbox{diode} \\ \mbox{source current} & T_{mb} = 25 \ {}^\circ\mbox{C} & [1] \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu s; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{ggedness} \\ \mbox{non-repetitive drain-source} & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ {}^\circ\mbox{C}; \ I_D = 120 \ A; \\ \end{array}$	$\begin{array}{cccc} drain-source \mbox{ voltage } & T_j \ge 25\ {}^\circ\mbox{C};\ T_j \le 175\ {}^\circ\mbox{C} & - & & & & \\ drain-gate \mbox{ voltage } & T_j \ge 25\ {}^\circ\mbox{C};\ T_j \le 175\ {}^\circ\mbox{C};\ R_{GS} = 20\ k\Omega & - & & \\ gate-source \mbox{ voltage } & & -20 & & \\ drain \mbox{ current } & V_{GS} = 10\ V;\ T_j = 100\ {}^\circ\mbox{C};\ see\ Figure\ 1 & - & \\ \hline V_{GS} = 10\ V;\ T_{mb} = 25\ {}^\circ\mbox{C};\ see\ Figure\ 1 & 1 & - & \\ \hline v_{GS} = 10\ V;\ T_{mb} = 25\ {}^\circ\mbox{C};\ see\ Figure\ 1 & 1 & - & \\ \hline peak\ drain\ current & pulsed;\ t_p \le 10\ \mu s;\ T_{mb} = 25\ {}^\circ\mbox{C};\ see\ Figure\ 2 & - & \\ storage\ temperature & & & -55 & \\ junction\ temperature & & & & -55 & \\ peak\ soldering\ temperature & & & & -55 & \\ peak\ soldering\ temperature & & & & & -& \\ \hline diode & & & & & \\ source\ current & T_{mb} = 25\ {}^\circ\mbox{C} & & & 11 & - & \\ pulsed;\ t_p \le 10\ \mu s;\ T_{mb} = 25\ {}^\circ\mbox{C} & & & -& \\ \hline gedness & & & & \\ non-repetitive\ drain-source & V_{GS} = 10\ V;\ T_{j(init)} = 25\ {}^\circ\mbox{C};\ I_D = 120\ A; & - & \\ \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

[1] Continuous current limited by package

PSMN4R3-100ES

PSMN4R3-100ES

N-channel 100 V 4.3 m Ω standard level MOSFET in I2PAK



N-channel 100 V 4.3 m Ω standard level MOSFET in I2PAK

5. Thermal characteristics

Table J.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

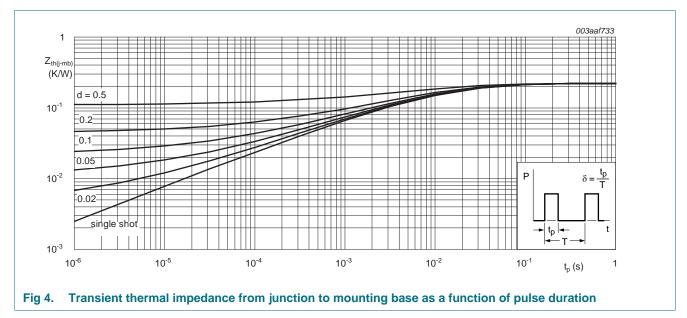


Table 5. Thermal characteristics

N-channel 100 V 4.3 mΩ standard level MOSFET in I2PAK

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	100	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.08	10	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R _{DSon} drain-source resistance	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	10.4	12	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13	-	6.6	7.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	<u>1]</u> -	3.7	4.3	mΩ
R _G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	170	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	140	-	nC
Q _{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	31	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	17.3	-	nC
Q _{GD}	gate-drain charge		-	49	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.1	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9900	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	660	-	pF
C _{rss}	reverse transfer capacitance		-	381	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_L = 0.67 Ω ; V_{GS} = 10 V;	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; I_D = 75 \ A; T_j = 25 \ ^{\circ}C$	-	91	-	ns
t _{d(off)}	turn-off delay time		-	122	-	ns
t _f	fall time		-	63	-	ns

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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	75	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$	-	235	-	nC

100

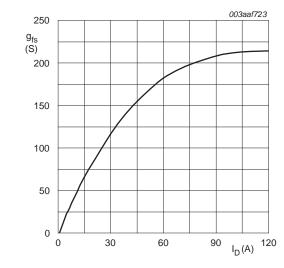
80

60

40

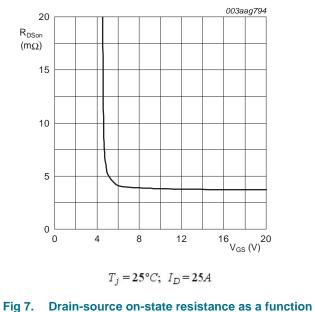
 I_{D} (Ā)

[1] Measured 3 mm from package.

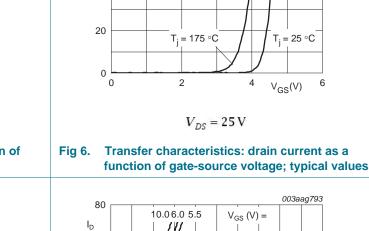


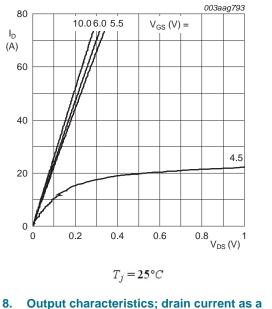
 $T_j = 25 \text{ °C}; V_{DS} = 25 \text{ V}$





of gate-source voltage; typical values





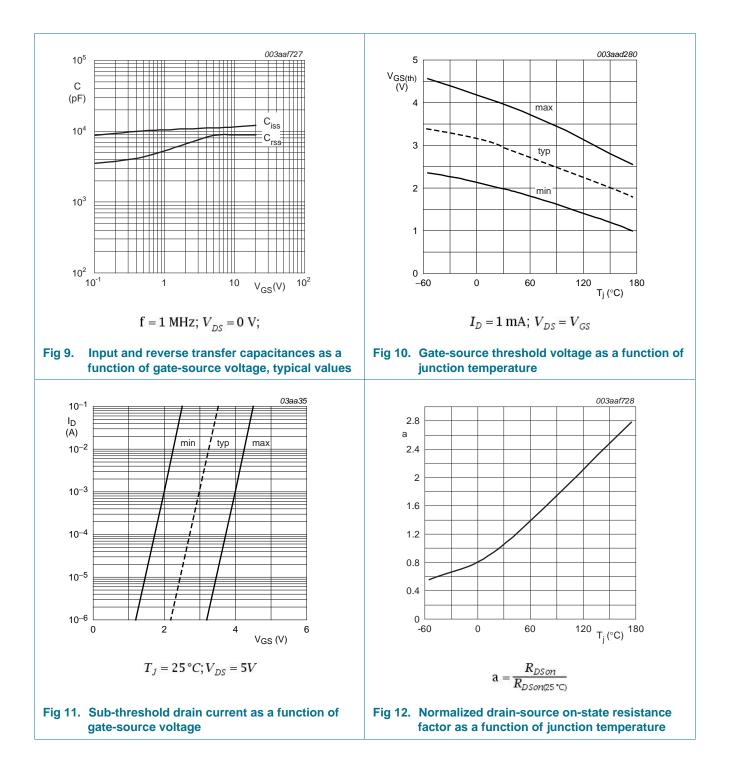


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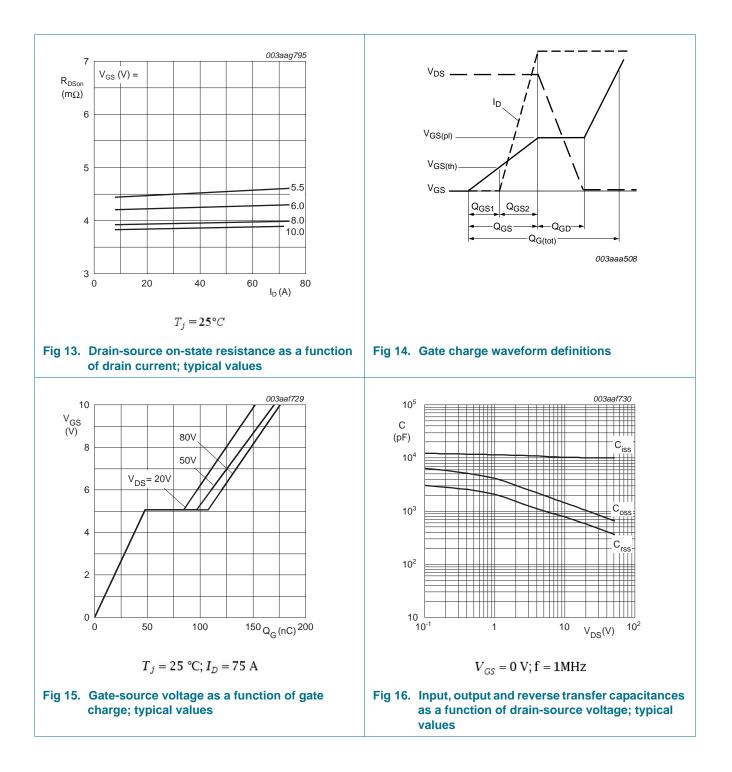
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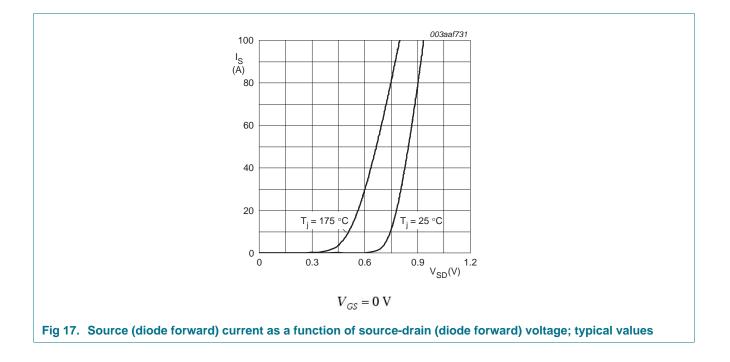
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N-channel 100 V 4.3 mΩ standard level MOSFET in I2PAK

7. Package outline

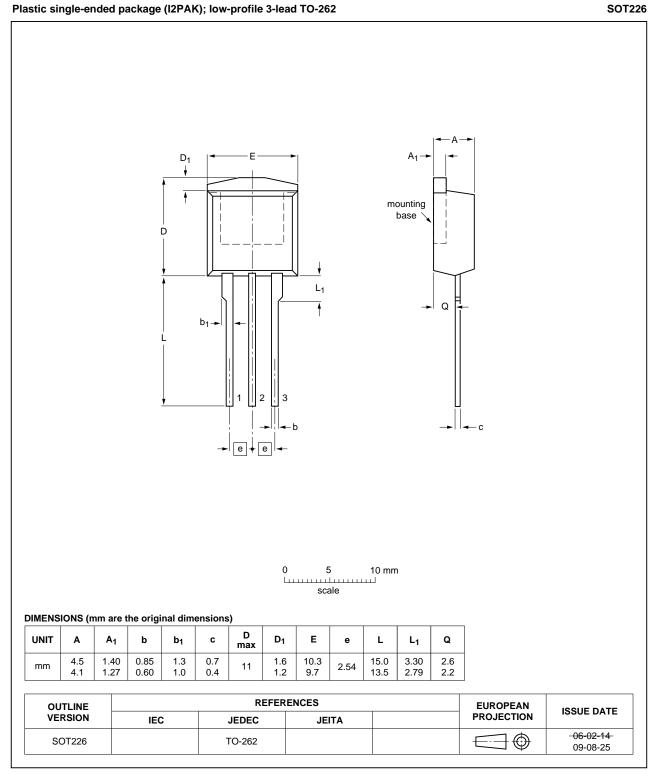


Fig 18. Package outline SOT226 (I2PAK)

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8. Revision history

Table 7. Revision h	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PSMN4R3-100ES v.1	20111031	Product data sheet	-	-			

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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